8-CHANNEL ANALOG MULTIPLEXER / DEMULTIPLEXER (SC1018-0T1) (Radiation Hardened)



Version 1.1, Jan' 2022



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PRODUCT DESCRIPTION:

The SC1018-0T1 is a Radiation Hardened 8-channel analog multiplexer de-multiplexer with three address inputs (S0 to S2), an active LOW enable input (\bar{E}) , eight independent inputs/outputs (Y0 to Y7) and a common input/output (Z). The device contains eight bidirectional analog switches, each with one side connected to an independent input/output (Y0 to Y7) and other side connected to a common input/output (Z).

 V_{DD} and V_{SS} are the supply voltage connections for the digital control inputs (S1 to S3, and $\bar{E}).$ The analog inputs/outputs (Y0 to Y7, and Z) can swing between V_{DD} as a positive limit and V_{SS} as negative limit.

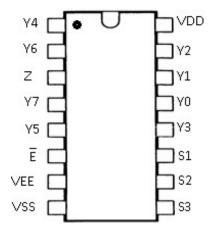
APPLICATIONS:

- Analog multiplexing and de-multiplexing
- Digital multiplexing and de-multiplexing
- Signal gating

Pin no.	Signal	Pin no.	Signal
1	Y4	9	S3
2	Y6	10	S2
3	Z	11	S1
4	Y7	12	Y3
5	Y5	13	Y0
6	Ē	14	Y1
7	$V_{\rm EE}$	15	Y2
8	V_{SS}	16	V_{DD}

FEATURES:

- Operating Voltage $5V \pm 0.5V$
- Low on resistance i.e. 200 ohm (Typ.)
- Low power dissipation (< 10uW at 5V static)
- Operating Ambient Temperature:
 -55°C to 125°C
- 16 pin CSOP/ Customized package / Die
- Pin compatible with CD4051
- Radiation Hardened up to 150 KRad TID
- SEL immune up to 70 MeV.cm²/mg.
- SET immune up to 52 MeV.cm²/mg
- Package $\Theta_{JC} = 3.1$ °C/Watt
- ESD Sensitivity Level:
 Class 0 (< 250V) HBM
- SCL's 180nm CMOS Technology



Device Pin diagram

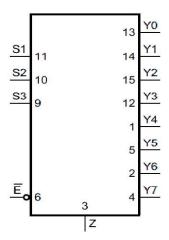


DEVICE PIN DESCRIPTION:

Symbol	Pin	Description
Ē	6	enable input (active LOW)
$ m V_{EE}$	7	supply voltage ($V_{EE} = 0V$)
$ m V_{SS}$	8	ground supply voltage (0V)
S1, S2, S3	11,10,9	select input
Y0, Y1, Y2, Y3, Y4, Y5, Y6, Y7	13, 14, 15, 12, 1, 5, 2, 4	independent input or output
Z	3	common output or input
$ m V_{DD}$	16	supply voltage

Signal description

LOGIC DIAGRAM (POSITIVE LOGIC):



Device Logic Diagram

FUNCTIONAL TABLE:

	Digital Inputs				
Ē	S3	S2	S1	Channel ON	
L	L	L	L	Y0 to Z	
L	L	L	Н	Y1 to Z	
L	L	Н	L	Y2 to Z	
L	L	Н	Н	Y3 to Z	
L	Н	L	L	Y4 to Z	
L	Н	L	Н	Y5 to Z	
L	Н	Н	L	Y6 to Z	
L	Н	Н	Н	Y7 to Z	
Н	X	X	X	Switches off	

Functional table



ABSOLUTE MAXIMUM RATINGS (1):

Over operating free-air temperature range (unless otherwise noted),

PARAMETER	UNIT
$ m V_{DD}$, Supply voltage range	-0.5 V to 6.5V
$V_{\mathrm{I}_{,}}$, Input voltage range	−0.5 V to 6.5 V
T _J , Operating Junction Temperature	+150 °C
T_{stg} , Storage temperature range	−65°C to 150°C

⁽¹⁾ Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

RECOMMENDED OPERATING CONDITIONS:

Symbol	Parameter	Min.	Тур.	Max.	Unit
V_{DD}	Supply voltage	4.5	5.0	5.5	V
V _{IN}	Input voltage range (Analog)	0	-	V_{DD}	V
V _{IH}	High level input voltage	$0.7 \times V_{DD}$	-	-	V
V _{IL}	Low level input voltage	-	-	$0.3 \times V_{DD}$	V
T _{AMB}	Operating Temperature	-55	-	+125	°C

DC ELECTRICAL SPECIFICATIONS:

Test condition: $V_{DD} = 5V \pm 0.5V$, $V_{SS} = V_{EE} = 0V$, $T_A = -55$ °C to +125°C (unless otherwise specified)

Symbol	Parameter	Test Conditions	Test Limits			Units
Symbol	1 urumeter	1 est conditions	Min.	Тур.	Max.	
I _{IIH}	Control Inputs (Digital) Leakage Current	$V_{DD} = 5.5 V, V_{IN} = V_{DD}$	-	0.02	±1	μА
I _{IIL}	Control Inputs (Digital) Leakage Current	$V_{DD} = 5.5 V, V_{IN} = V_{SS}$	1	0.02	±2	μА
T.	Off State Leakage Current	$\begin{split} \bar{E} &= V_{DD}, \\ V_{DD} &= 5.5 V, V_{IN} = V_{DD} \end{split}$	1	0.01	±1	μА
I _{S(OFF)} Z Port (all channels OFF) or Y Port (per channel)	$\begin{split} \bar{E} &= V_{DD}, \\ V_{DD} &= 5.5 V, V_{IN} = 0 \end{split}$	-	0.01	±1	μА	
R _{ON}	Channel ON Resistance (rail)	$V_{DD} = 5.0V$, $V_{IN} = 0V$ or 5.0V, Channel selected	100	200	400	ohm
	Static Supply Current (Device Enable)	$V_{DD} = 5V \pm 0.5V$	-	4.16	20	uA
I _{DD}	Static Supply Current (Device Disable)	$I_{O} = 0$ mA	-	3.97	20	uA

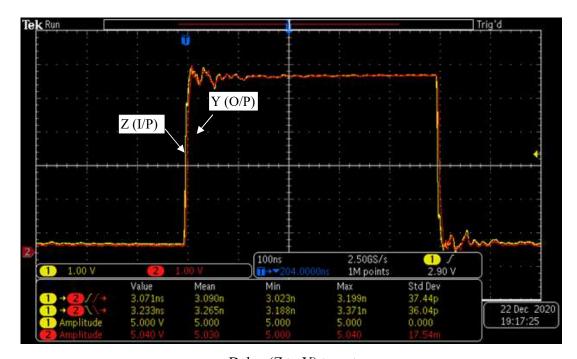


AC ELECTRICAL SPECIFICATIONS:

 $\textbf{Test condition:} \ V_{DD} = 5V, \ V_{IN} = 0V \ or \ 5V \ @1 \ MHz, \ C_L = 10pF, \ R_L = 10K\Omega, \ T_{AMB} = 22 \pm 3^{\circ}C$

Symbol	Parameter	From	То	Test Results (Typ.)	Max.	Units
t _{PLH}	LOW to HIGH propagation delay	Z	Y	3.07	15	ns
t _{PHL}	HIGH to LOW propagation delay			3.23	15	ns
t_{PZL}	OFF-state to LOW propagation delay	Ē O/P	3.8	15	ns	
t_{PLZ}	LOW to OFF-state propagation delay	L	O/F	5.6	15	ns
t _{PZH}	OFF-state to HIGH propagation delay	Ē	O/P	3.2	15	ns
$t_{ m PHZ}$	HIGH to OFF-state propagation delay	E O/P		16.8	40	ns
f _{ON}	-3dB Cut off frequency (Channel ON) $CL = 5pF,RL=1K\Omega$	-	-	103		Mhz
THD	Total Harmonic Distortion $CL = 5pF,RL=1K\Omega$	-	-	0.723	-1	%

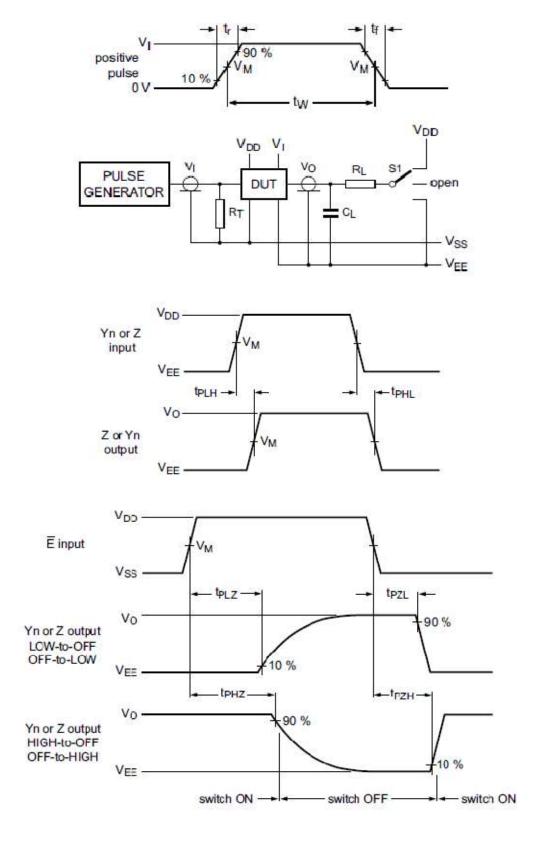
AC Electrical Specification



Delay (Z to Y) t_{PLH} , t_{PHL}

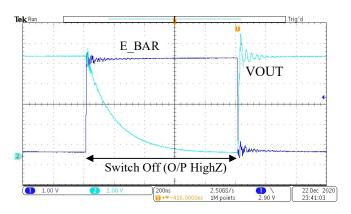


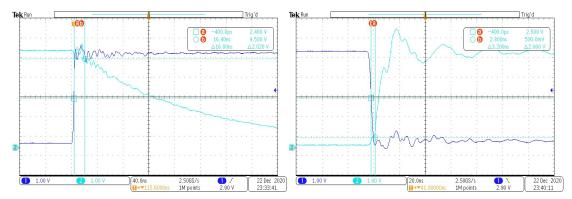
TEST CIRCUIT AND SWITCHING WAVEFORM FOR DELAY MEASURMENTS:



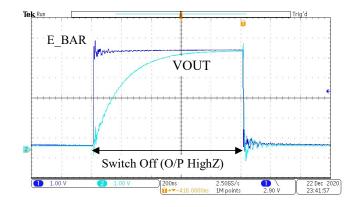


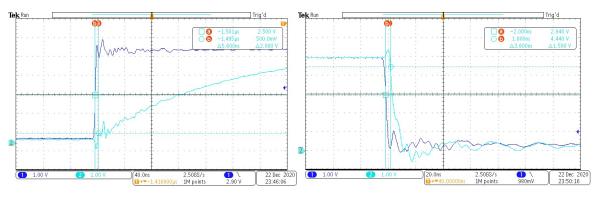
High Z Delay waveforms (t_{PZH}/t_{PHZ}):





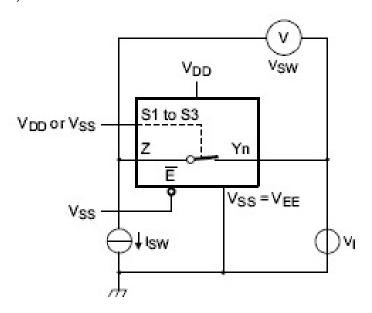
High Z Delay waveforms (t_{PZL}/t_{PLZ}):



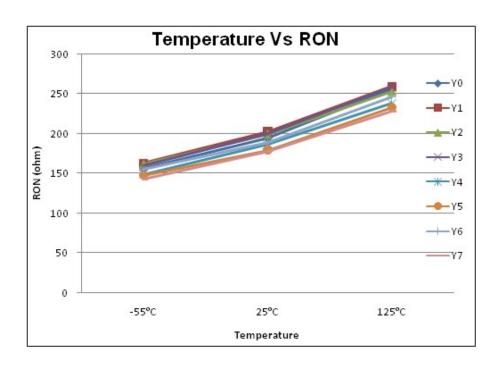




Test Circuit (RON):

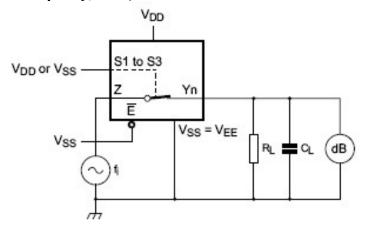


Test circuit for measuring R_{ON} , ($R_{ON} = V_{SW} / I_{SW}$)

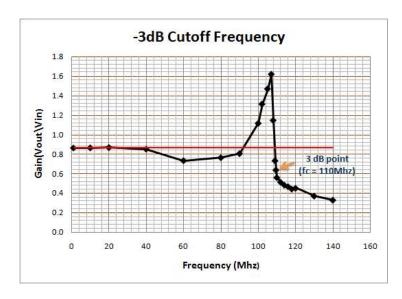


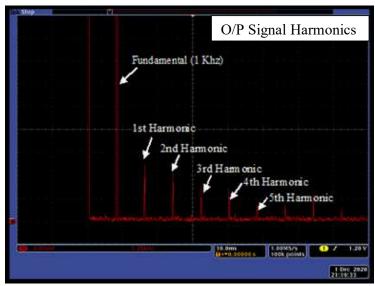


Test Circuit (Cutoff frequency, THD):



Test circuit for measuring frequency response and total harmonic distortion





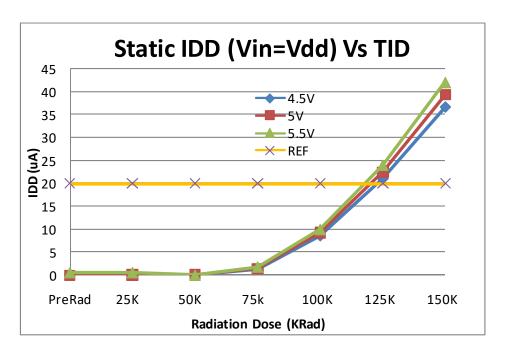


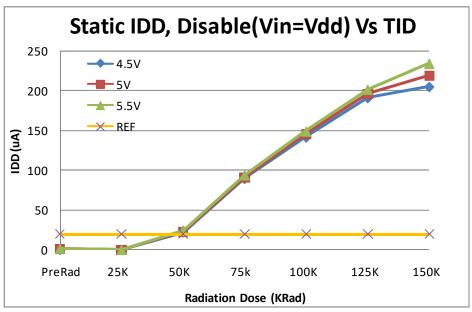
RADIATION TESTING

Total Dose (TID)

SC1018-0T1 is tested and characterized between dose rate of 50 and 300 rad/s (full CMOS technology). TID testing is conducted up to cumulative dose of 150 KRad. No functional failure observed upto 150 KRad.

RADIATION CHARACTERISTICS:







Heavy Ions (SET)

- SEE testing of SC1018-0T1 is completed at three different ion beams of LET 30, LET 52 and 70.7 MeV-cm2/mg for a Fluence of 10⁶ ions/ cm².
- No SEL is observed for LET up to 70.4 MeV- cm²/mg.
- No SET is observed for LET up to 52 MeV- cm²/mg.

Radiation Type	Characteristics	Value	Unit
TID	High-dose rate (50 - 300 rad/sec) up to:	150	kRad
Haarwii aaa	SEL immune up to:	70	MeV-cm ² /mg
Heavy ions	SET immune up to:	52	Mev-cm/mg

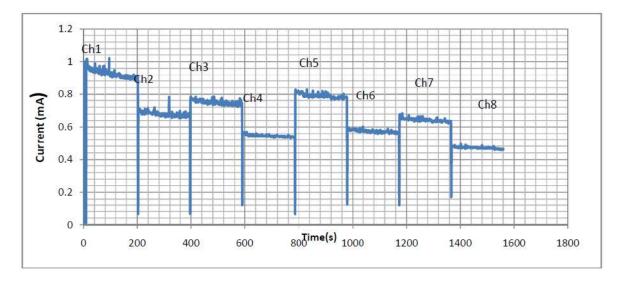


Figure: MUX Current Monitoring at LET-70 MeV-cm2/mg

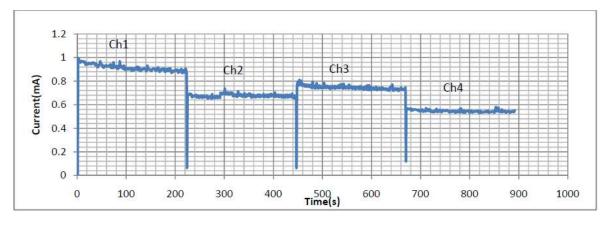
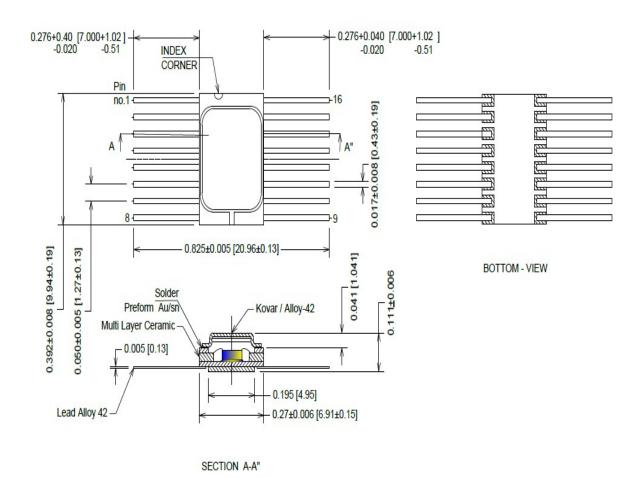


Figure: DEMUX Current Monitoring at LET-70 MeV-cm2/mg

PACKAGE DRAWING (CSOP-16):



	Revision History				
S. No.	Version	Date of release	Description		
1	1.0	Dec. 2020			
2	1.1	Jan. 2022	Radiation test results added, page-10		

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